

深圳市晶泰源电子有限公司

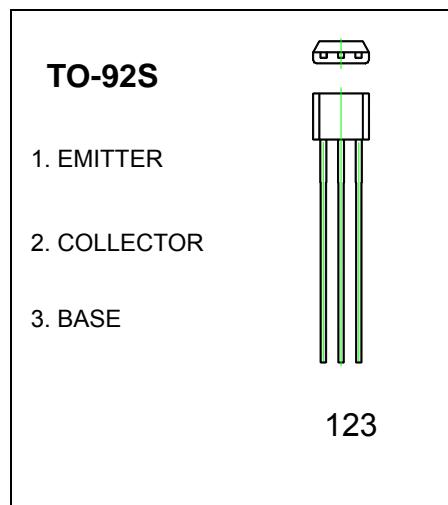
KTC3195 TRANSISTOR (NPN)

FEATURES

- Small reverse transfer capacitance $C_{re}=0.7\text{pF}(\text{Typ})$
- Low noise Figure: $NF=2.5\text{dB}(\text{Typ.})$

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Value | Units |
|-----------|-------------------------------|---------|------------------|
| V_{CBO} | Collector-Base Voltage | 40 | V |
| V_{CEO} | Collector-Emitter Voltage | 30 | V |
| V_{EBO} | Emitter-Base Voltage | 4 | V |
| I_C | Collector Current -Continuous | 20 | mA |
| P_c | Collector Power Dissipation | 400 | mW |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature | -55-150 | $^\circ\text{C}$ |



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test conditions | MIN | TYP | MAX | UNIT |
|-------------------------------------|---------------|---|-----|-----|-----|---------------|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C=100\mu\text{A}, I_E=0$ | 40 | | | V |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | $I_C=1\text{mA}, I_B=0$ | 30 | | | V |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | $I_E=100\mu\text{A}, I_C=0$ | 4 | | | V |
| Collector cut-off current | I_{CBO} | $V_{CB}=40\text{V}, I_E=0$ | | | 0.5 | μA |
| Emitter cut-off current | I_{EBO} | $V_{EB}=4\text{V}, I_C=0$ | | | 0.5 | μA |
| DC current gain | $h_{FE(1)}$ | $V_{CE}=6\text{V}, I_C=1\text{mA}$ | 40 | | 200 | |
| Transition frequency | f_T | $V_{CE}=6\text{V}, I_C=1\text{mA}$ | 300 | 550 | | MHz |
| Reverse Transfer capacitance | C_{re} | $V_{CB}=6\text{V}, I_E=0, f=1\text{MHz}$ | | 0.7 | | pF |
| Noise figure | NF | $V_{CE}=6\text{V}, I_C=1\text{mA}, f=100\text{MHz}$ | | 2.5 | 5 | dB |
| Power Gain | G_{pe} | | | 18 | | dB |

CLASSIFICATION OF $h_{FE(1)}$

| | | | |
|---------|--|--|---------|
| Rank | | | Y |
| Range | | | 100-200 |
| Marking | | | |